What is Claimed:

1. A method of packaging a semiconductor device, the method comprising the steps of:

applying an insulative material across only a portion of at least two of a plurality of conductors providing interconnection between elements in the semiconductor device; and

encapsulating the conductors and elements, thereby packaging the semiconductor device.

2. The method of claim 1 further comprising the step of:

curing the insulative material after said applying step.

3. The method of claim 2 wherein said curing step includes at least one of heating the insulative material and exposing the insulative material to UV radiation.

4. The method of claim 1 wherein said applying step includes applying an insulative compound comprising spherical silica particles to the portion of a plurality of conductors.

5. The method of claim 4 wherein the insulative compound is applied in a substantially circumferential manner about an inner element of the semiconductor device.

6. The method of claim 4 wherein the insulative compound is applied in at least two geometric shape structures, each of the geometric shape structures substantially surrounding an inner element of the semiconductor device in a circumferential manner.

7. The method of claim 1 wherein said applying step includes applying a solid insulator having an adhesive backing to the

portion of a plurality of conductors such that the adhesive backing is in contact with the portion of a plurality of conductors.

8. The method of claim 1 wherein said applying step includes applying an insulative tape to the portion of a plurality of conductors.

9. The method of claim 1 wherein said applying step includes applying a continuous bead of the insulative material across only a portion of at least two of a plurality of conductors providing interconnection between elements in the semiconductor device.

10. The method of claim 1 wherein said applying step includes applying the insulative material around a peripheral portion of an inner element of the semiconductor device.

11. The method of claim 1 wherein said applying step includes applying the insulative material in at least two distinct structures around a peripheral portion of an inner element of the semiconductor device, the two structures not being in contact with one another.

12. A semiconductor device comprising:

a plurality of semiconductor elements;

a plurality of conductors providing interconnection between said plurality of semiconductor elements; and

an insulative material applied across only a portion of at least two of said plurality of conductors.

13. The semiconductor device of claim 12 further comprising an encapsulation layer encapulating said conductors and elements for packaging said semiconductor device.

14. The semiconductor device of claim 12 wherein said plurality of semiconductor elements includes at least one semiconductor die having a plurality of first contacts, and a lead frame having a plurality of second contacts, said plurality of conductors providing interconnection between said plurality of first contacts and said plurality of second contacts.

15. The semiconductor device of claim 14 wherein said insulative material is disposed across said portion of said at least two of said plurality of conductors adjacent said semiconductor die.

16. The semiconductor device of claim 14 wherein said insulative material is disposed across said portion of said at least two of said plurality of conductors approximately midway between said semiconductor die and said leadframe.

17. The semiconductor device of claim 12 wherein said insulative material is a curable insulative material.

18. The semiconductor device of claim 12 wherein said insulative material is at least one of a heat induced curable insulative material and a UV radiation curable insulative material.

19. The semiconductor device of claim 12 wherein said insulative material is comprised of a plurality of spherical silica particles.

20. The semiconductor device of claim 12 wherein said insulative material is applied around a peripheral portion of an inner element of said semiconductor device.

21. The semiconductor device of claim 12 wherein said insulative material is applied in at least two distinct structures around a peripheral portion of an inner element of said semiconductor device, said two structures not being in contact with one another.

22. The semiconductor device of claim 12 wherein said insulative material includes a substantially solid insulator having an adhesive component such that said adhesive component is in contact with said portion of said at least two of said plurality of conductors.

23. The semiconductor device of claim 12 wherein said insulative material is an insulative tape.